

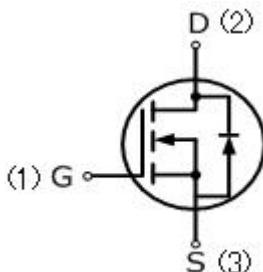


## MIC-IRF830

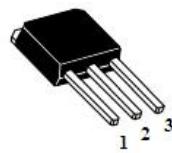
### 5 Amps, 500 Volts N-CHANNEL MOSFET

#### FEATURE

- 5A, 500V,  $R_{DS(ON)} \text{MAX} = 1.5 \Omega$  @  $V_{GS} = 10V/2.5A$
- Low gate charge
- Low  $C_{iss}$
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-252



TO-251

#### Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	MIC-IRF830	UNIT
Drain-Source Voltage	$V_{DSS}$	500	V
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	
Continuous Drain Current	$I_D$	5	A
Pulsed Drain Current (Note 1)	$I_{DM}$	20	
Single Pulse Avalanche Energy (Note 2)	$E_{AS}$	250	mJ
Reverse Diode dV/dt (Note 3)	dV/dt	5	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	$T_L$	260	°C

#### Thermal Characteristics

Parameter	Symbol	TO-252/251	Units
Thermal resistance, Channel to Case	$R_{th(ch-c)}$	1.67	°C/W
Thermal resistance, Channel to Ambient	$R_{th(ch-a)}$	100	°C/W
Maximum Power Dissipation	$T_c = 25^\circ\text{C}$	75	W



## Electrical Characteristics ( $T_c=25^\circ\text{C}$ ,unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	500	—	—	V
Breakdown Temperature Coefficient	$\Delta\text{BV}_{\text{DSS}}/\Delta T_J$	Reference to $25^\circ\text{C}$ , $\text{I}_D=250\mu\text{A}$	—	0.6	—	$\text{V}/^\circ\text{C}$
Zero Gate Voltage Drain Current	$\text{I}_{\text{DS}}^{\text{SS}}$	$\text{V}_{\text{DS}}=500\text{V}, \text{V}_{\text{GS}}=0\text{V}$	—	—	1	$\mu\text{A}$
Gate-Body Leakage Current,Forward	$\text{I}_{\text{GSS}}$	$\text{V}_{\text{GS}}=30\text{V}, \text{V}_{\text{DS}}=0\text{V}$	—	—	100	nA
Gate-Body Leakage Current,Reverse	$\text{I}_{\text{GSR}}$	$\text{V}_{\text{GS}}=-30\text{V}, \text{V}_{\text{DS}}=0\text{V}$	—	—	-100	nA
<b>On Characteristics</b>						
Gate-Source Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	2	—	4	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(on)}}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=2.5\text{A}$	—	1.3	1.5	$\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$\text{C}_{\text{iss}}$	$\text{V}_{\text{DS}}=25\text{V}, \text{V}_{\text{GS}}=0\text{V},$ $f=1.0\text{MHZ}$	—	584	—	pF
Output Capacitance	$\text{C}_{\text{oss}}$		—	61	—	pF
Reverse Transfer Capacitance	$\text{C}_{\text{rss}}$		—	4	—	pF
<b>Switching Characteristics</b>						
Turn-On Delay Time	$t_{d(\text{on})}$	$\text{V}_{\text{DD}}=250\text{V}, \text{I}_D=5\text{A},$ $\text{R}_G=10\Omega$ (Note3,4)	—	14	—	ns
Turn-On Rise Time	$t_r$		—	18	—	ns
Turn-Off Delay Time	$t_{d(\text{off})}$		—	32	—	ns
Turn-Off Fall Time	$t_f$		—	11	—	ns
Total Gate Charge	$\text{Q}_g$	$\text{V}_{\text{DS}}=400\text{V}, \text{I}_D=5\text{A},$ $\text{V}_{\text{GS}}=10\text{V}, (\text{Note3,4})$	—	12.6	—	nC
Gate-Source Charge	$\text{Q}_{gs}$		—	3.1	—	nC
Gate-Drain Charge	$\text{Q}_{gd}$		—	4.9	—	nC
<b>Drain-Source Body Diode Characteristics and Maximum Ratings</b>						
Continuous Diode Forward Current	$\text{I}_S$		—	—	5	A
Pulsed Diode Forward Current	$\text{I}_{\text{SM}}$		—	—	20	A
Diode Forward Voltage	$\text{V}_{\text{SD}}$	$\text{I}_S=5\text{A}, \text{V}_{\text{GS}}=0\text{V}$	—	—	1.5	V
Reverse Recovery Time	$t_{rr}$	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_S=5\text{A},$ $d\text{I}_F/dt=100\text{A/us}, (\text{Note4})$	—	328	—	ns
Reverse Recovery Charge	$\text{Q}_{rr}$		—	1555	—	$\mu\text{C}$

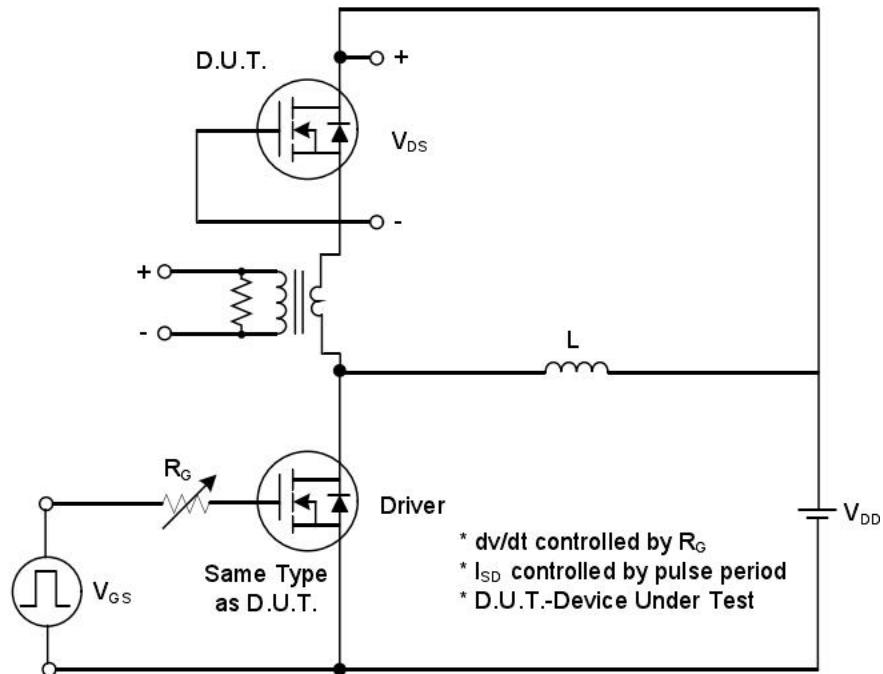
### Notes

1. Repetitive Rating:pulse width limited by maximum junction temperature.
2.  $L=10\text{mH}, \text{I}_{AS}=7.1\text{A}$ ,starling  $T_J=25^\circ\text{C}$ .
3.  $\text{I}_{SD}=5\text{A}, d\text{I}/dt \leq 100\text{A/us}, \text{V}_{\text{DD}} \leq \text{BV}_{\text{DSS}}$ ,starting  $T_J=25^\circ\text{C}$ ,Pulse width $\leq 300\text{us}$ ;duty cycle $\leq 2\%$ .
4. Repetitive rating: pulse width limited by maximum junction temperature.

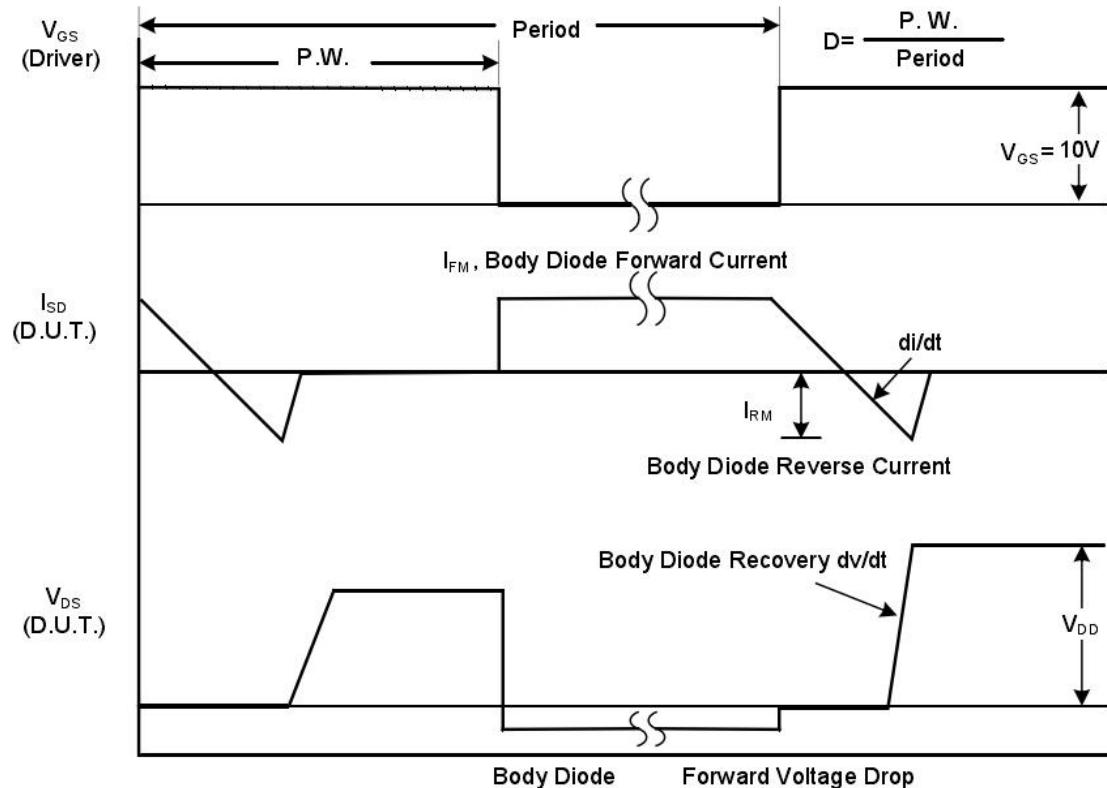


## TEST CIRCUIT AND WAVEFORM

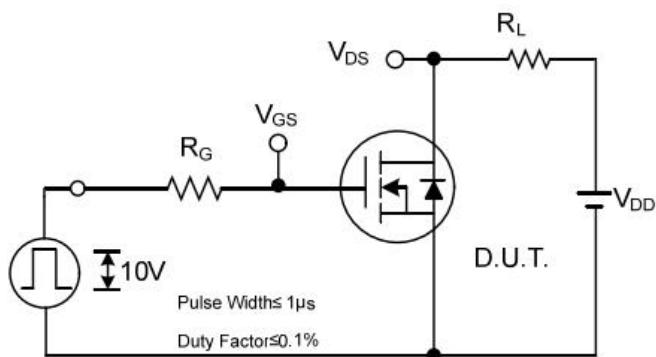
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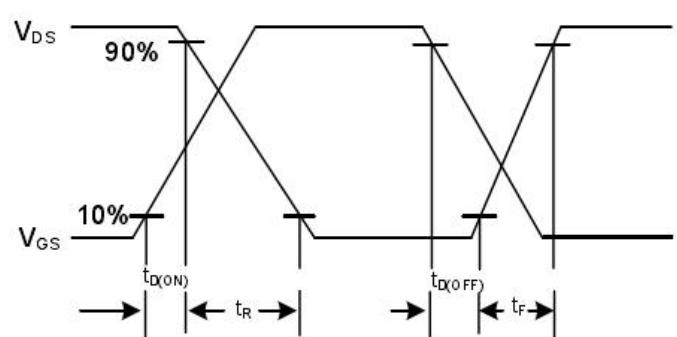
Peak Diode Recovery  $dv/dt$  Test Circuit



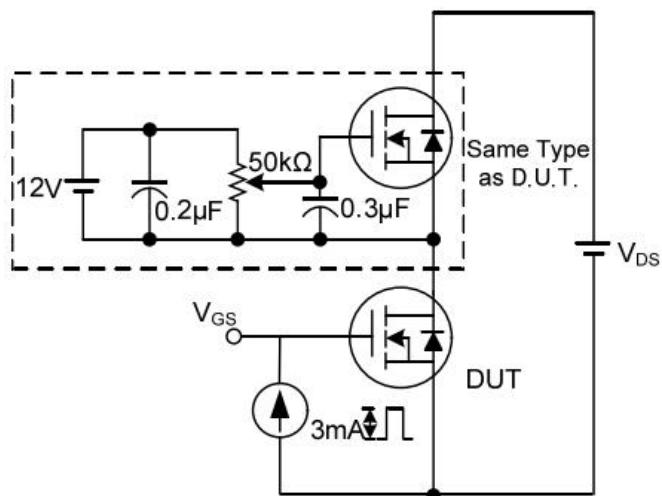
Peak Diode Recovery  $dv/dt$  Waveforms



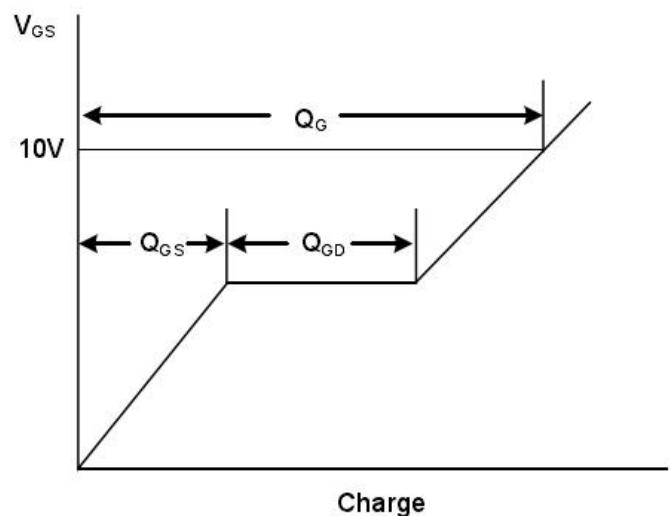
**Switching Test Circuit**



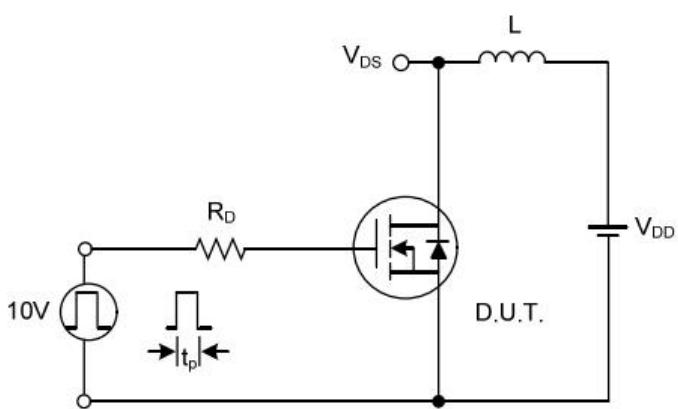
**Switching Waveforms**



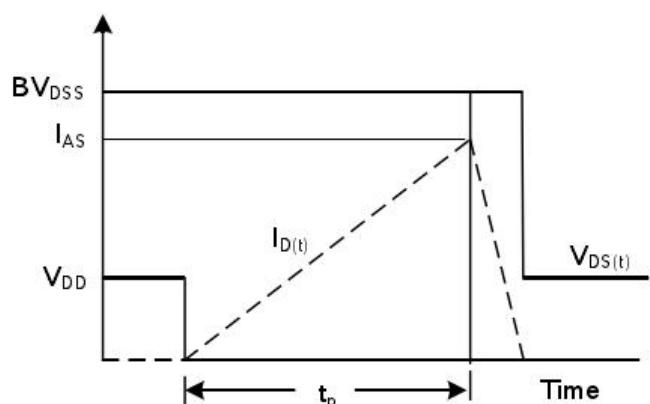
**Gate Charge Test Circuit**



**Gate Charge Waveform**



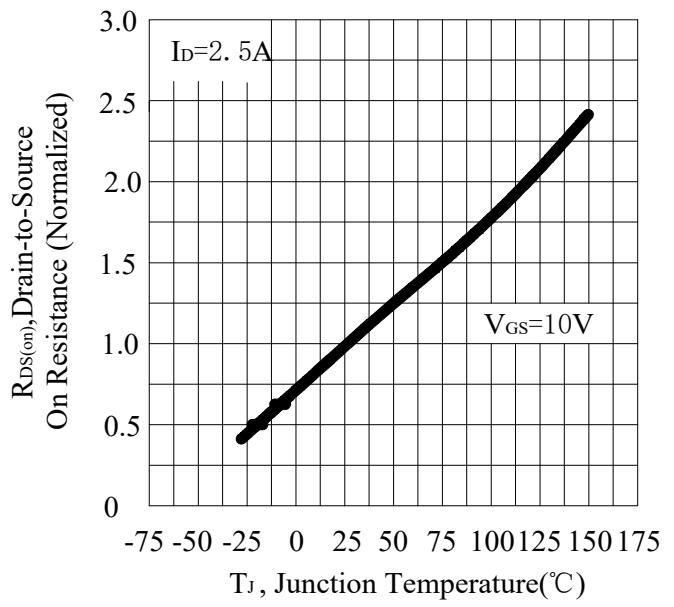
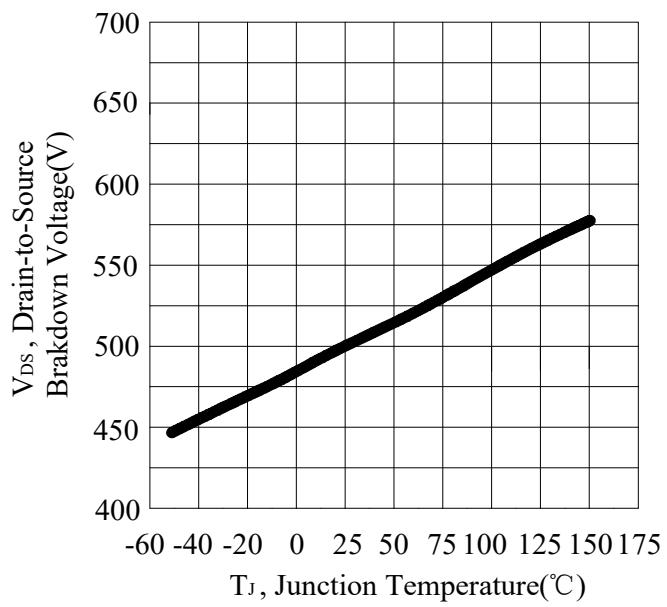
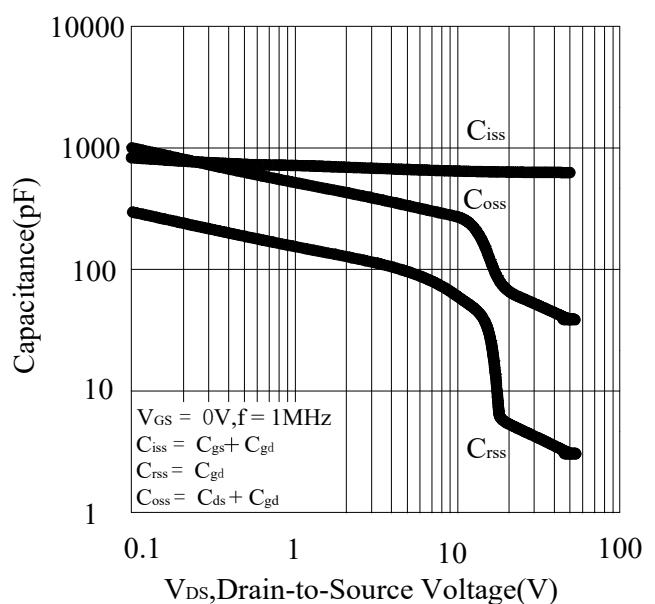
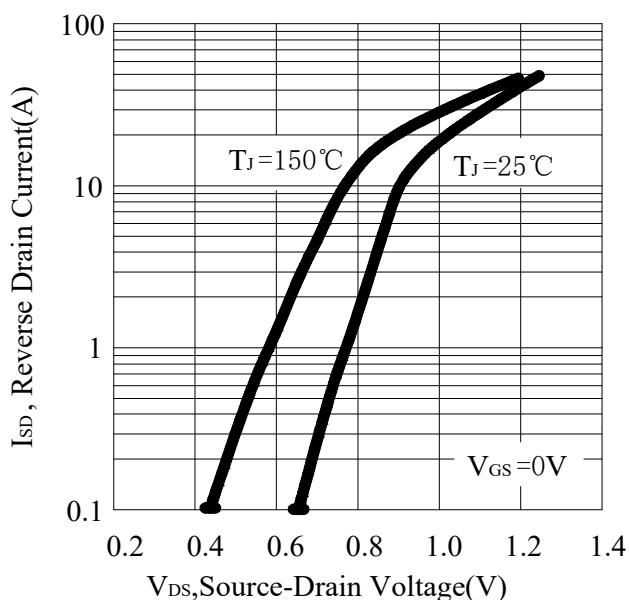
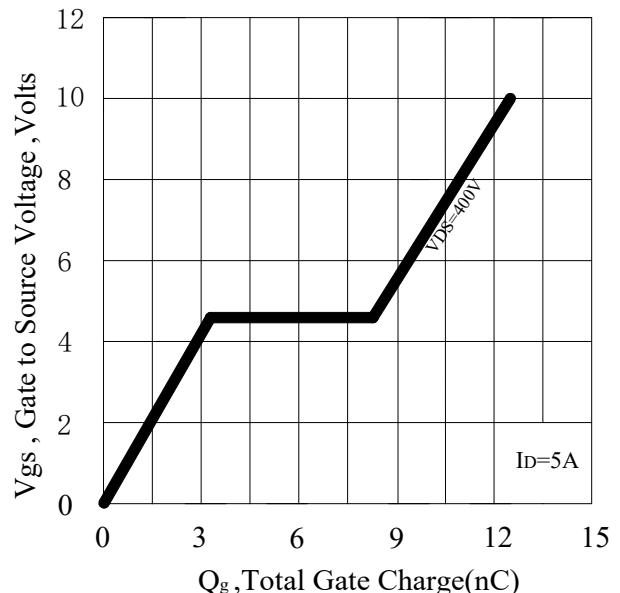
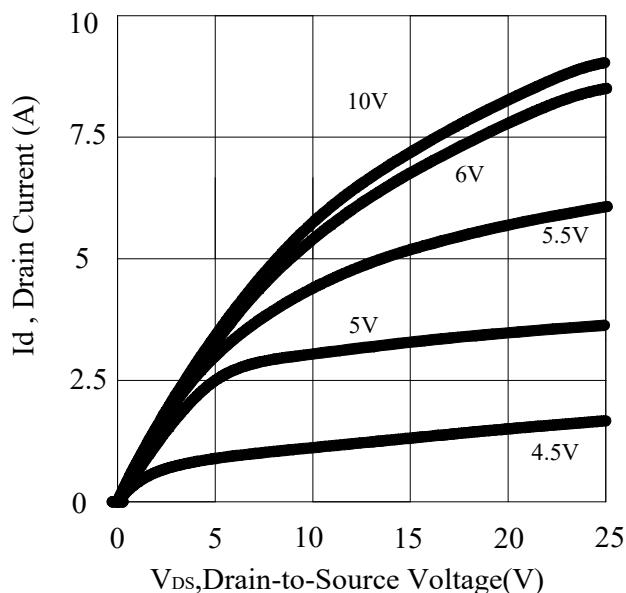
**Unclamped Inductive Switching Test Circuit**

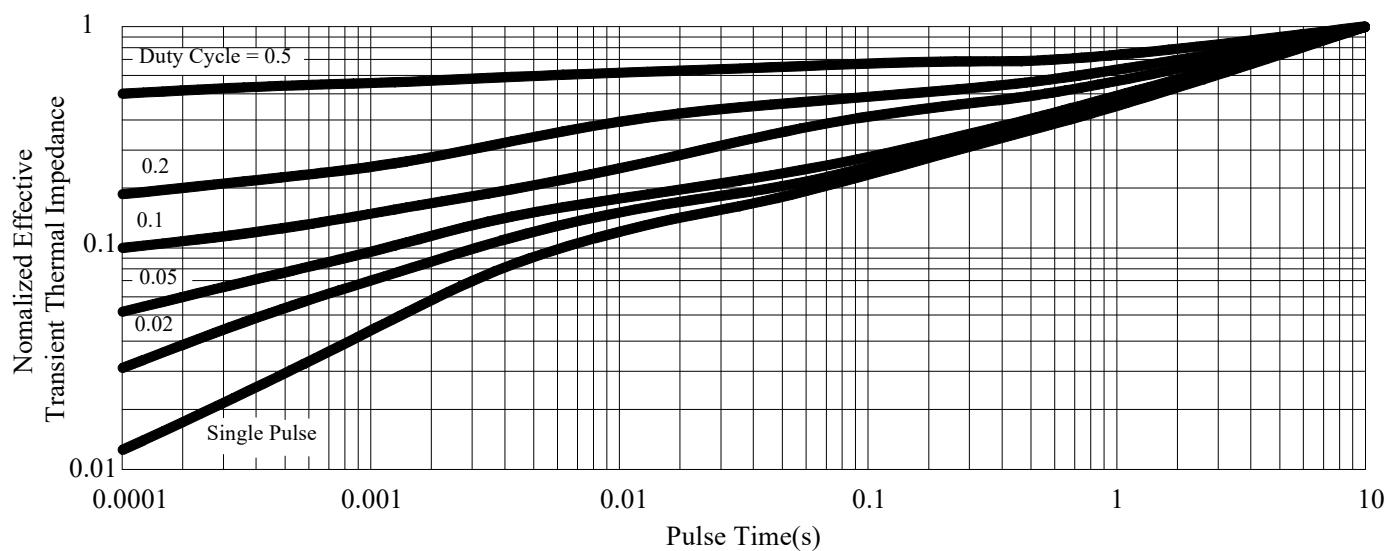
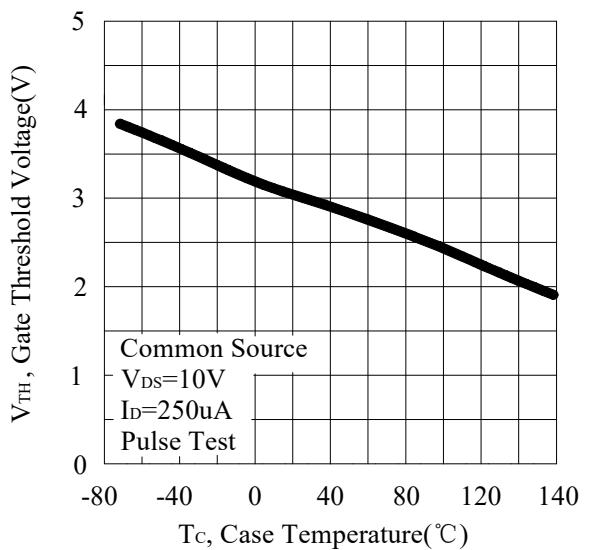
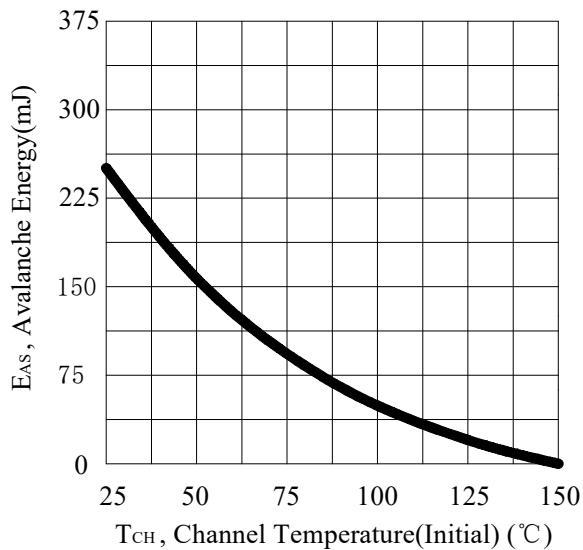
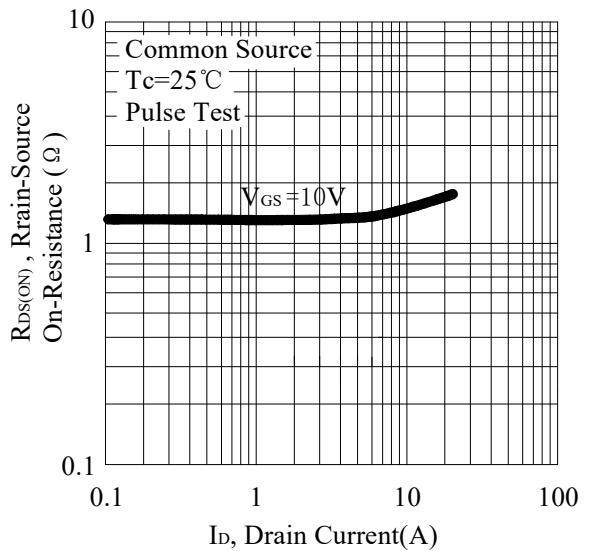
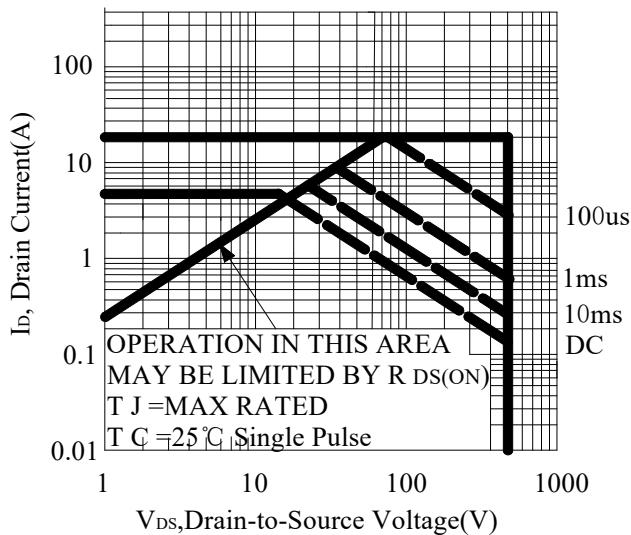


**Unclamped Inductive Switching Waveforms**



## RATING AND CHARACTERISTIC CURVES

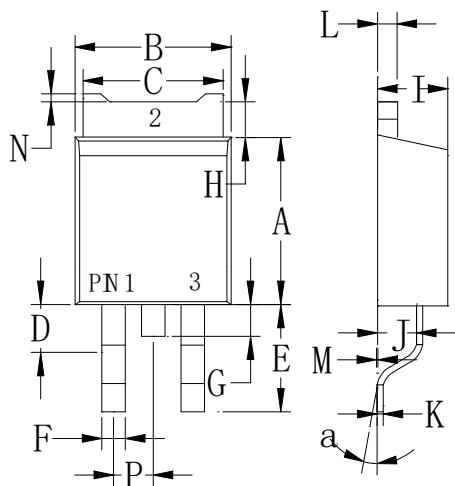






## PACKAGE OUTLINE DIMENSIONS

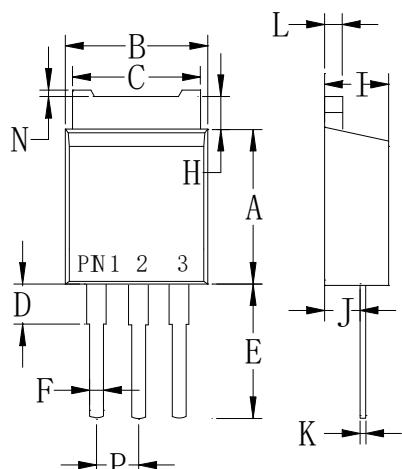
TO-252



TO-252		
Dim	Min	Max
A	.230 (5.85)	.246 (6.25)
B	.250 (6.35)	.264 (6.75)
C	.207 (5.27)	.218 (5.54)
D	.037 (0.93)	.045 (1.14)
E	.106 (2.70)	.138 (3.50)
F	.028 (0.72)	.033 (0.84)
G	.024 (0.60)	.041 (1.05)
H	.028 (0.72)	.043 (1.10)
I	.085 (2.15)	.096 (2.45)
J	.037 (0.95)	.047 (1.20)
K	.018 (0.45)	.026 (0.65)
L	.018 (0.45)	.024 (0.60)
P	.081 (2.05)	.094 (2.40)
M	.000 (0.00)	.006 (0.15)
N	--	.008 (0.20)
a	0°	10°

Dimensions in inches and (millimeters)

TO-251



TO-251		
Dim	Min	Max
A	.230 (5.85)	.246 (6.25)
B	.250 (6.35)	.266 (6.75)
C	.207 (5.27)	.218 (5.54)
D	.037 (0.93)	.045 (1.14)
E	.173 (4.40)	.205 (5.20)
F	.028 (0.72)	.033 (0.84)
H	.028 (0.70)	.043 (1.10)
I	.085 (2.15)	.096 (2.45)
J	.037 (0.95)	.047 (1.20)
K	.018 (0.45)	.026 (0.65)
L	.018 (0.45)	.024 (0.60)
N	--	.008 (0.20)
P	.081 (2.05)	.094 (2.40)

Dimensions in inches and (millimeters)